



SamHop Microelectronics Corp.

STG8207

Dec 27, 2004 ver1.2

Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	8 A	16 @ V _{GS} = 4.5V 24 @ V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous ^a @ T _J =25°C	I _D	8	A
	I _{DM}	42	A
Drain-Source Diode Forward Current ^a	I _S	2	A
Maximum Power Dissipation ^a	P _D	1.5	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	85	°C/W
--	------------------	----	------

STG8207

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 5A$		12	16	m ohm
		$V_{GS} = 2.5V, I_D = 3A$		20	24	m ohm
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 5A$		17		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{iss}	$V_{DS} = 8V, V_{GS} = 0V$ $f = 1.0MHz$		1800		pF
Output Capacitance	C_{oss}			400		pF
Reverse Transfer Capacitance	C_{rss}			320		pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 10V$ $I_D = 1A$ $V_{GEN} = 4.5V$ $R_L = 10 \text{ ohm}$ $R_{GEN} = 10 \text{ ohm}$		58.5		ns
Rise Time	t_r			16		ns
Turn-Off Delay Time	$t_{D(OFF)}$			110.5		ns
Fall Time	t_f			45.8		ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 5A$ $V_{GS} = 4.5V$		27		nC
Gate-Source Charge	Q_{gs}			3.8		nC
Gate-Drain Charge	Q_{gd}			7.8		nC

STG8207

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 2A$		0.78	1.2	V

Notes

a. Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.

b. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

c. Guaranteed by design, not subject to production testing.

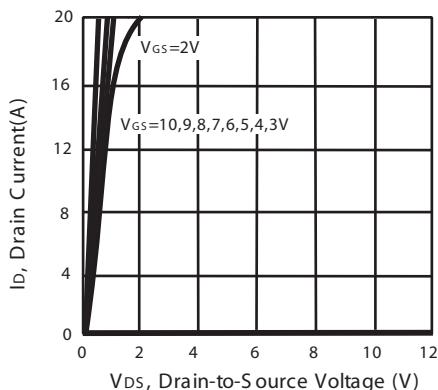


Figure 1. Output Characteristics

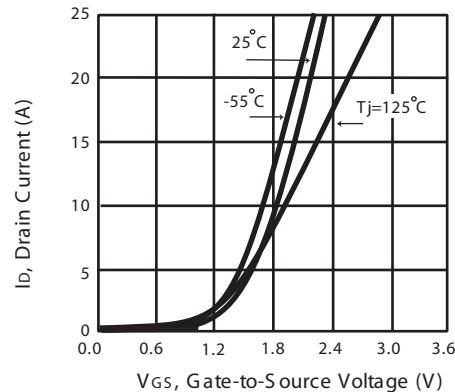


Figure 2. Transfer Characteristics

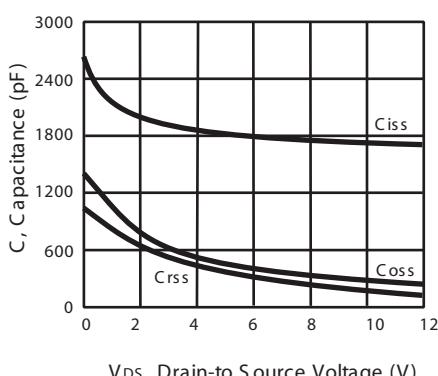


Figure 3. Capacitance

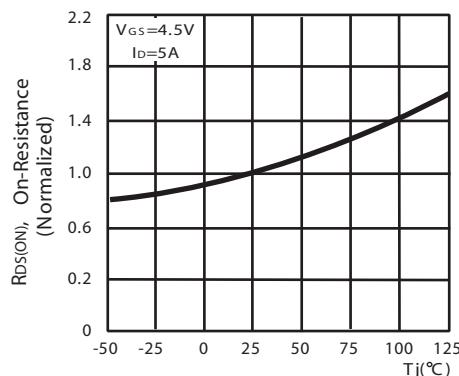


Figure 4. On-Resistance Variation with Temperature

STG8207

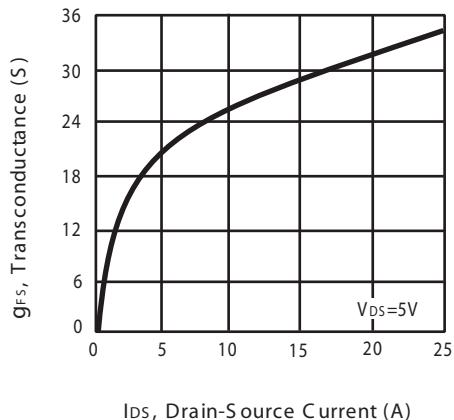
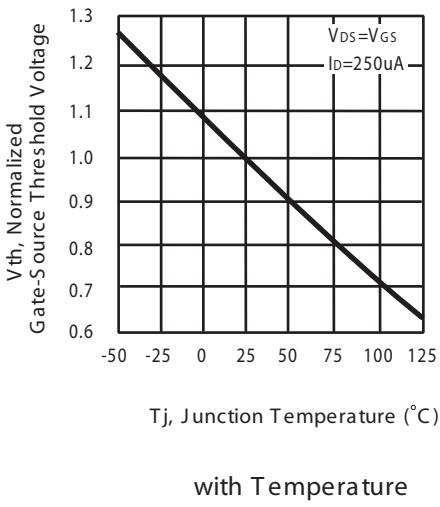


Figure 7. Transconductance Variation with Drain Current

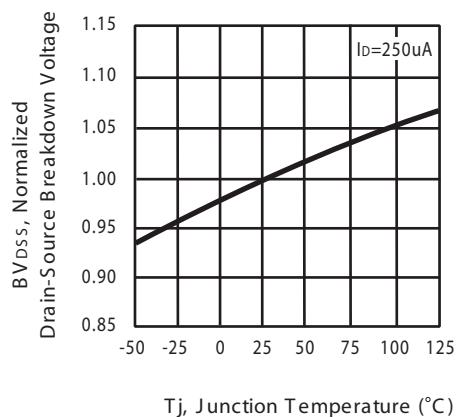


Figure 6. Breakdown Voltage Variation with Temperature

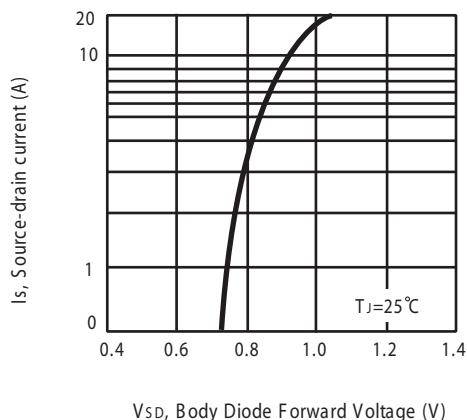


Figure 8. Body Diode Forward Voltage Variation with Source Current

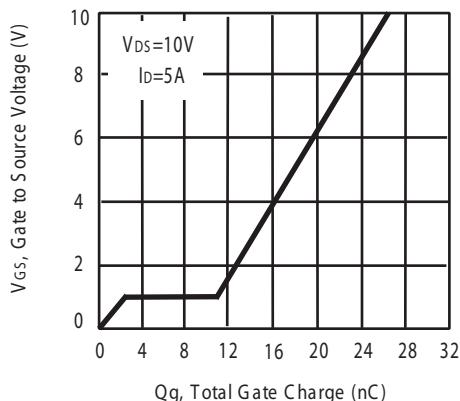


Figure 9. Gate Charge

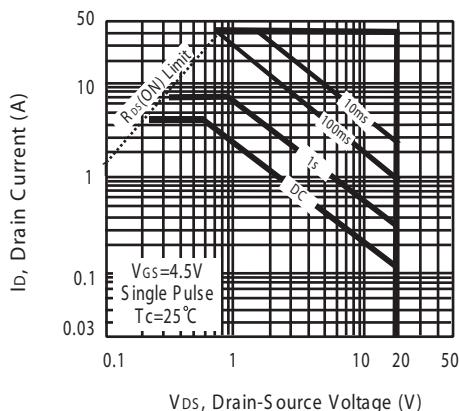
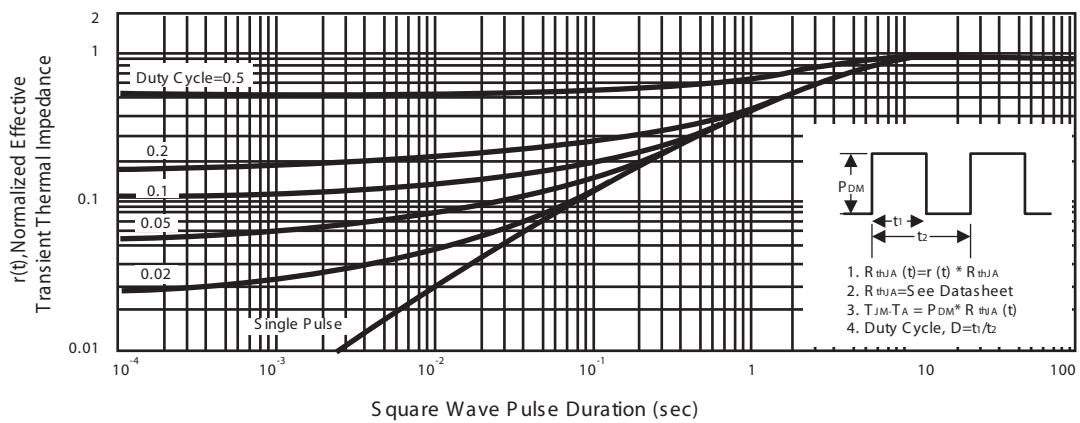
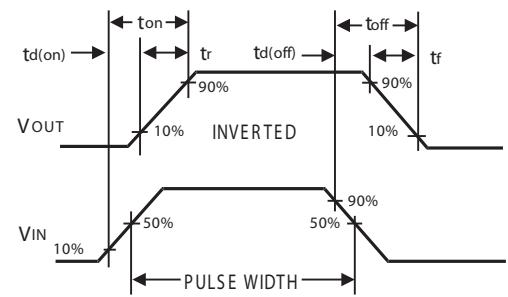
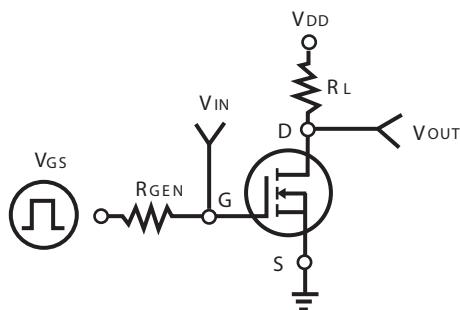


Figure 10. Maximum Safe Operating Area

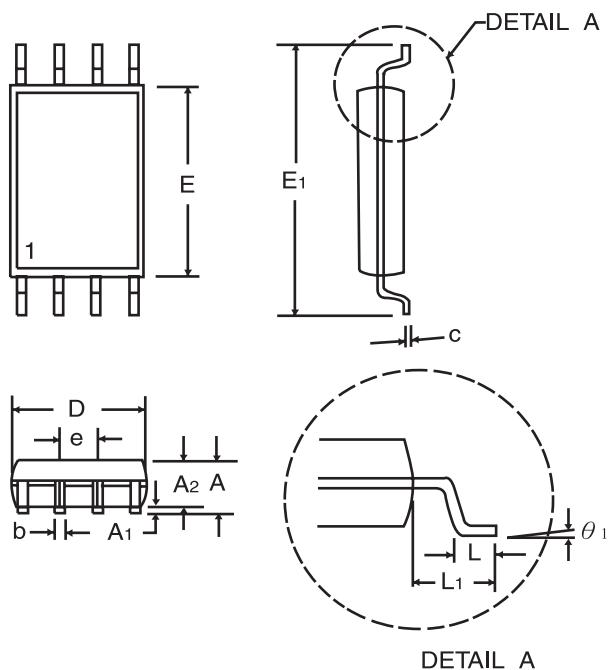
STG8207



STG8207

PACKAGE OUTLINE DIMENSIONS

TSSOP-8

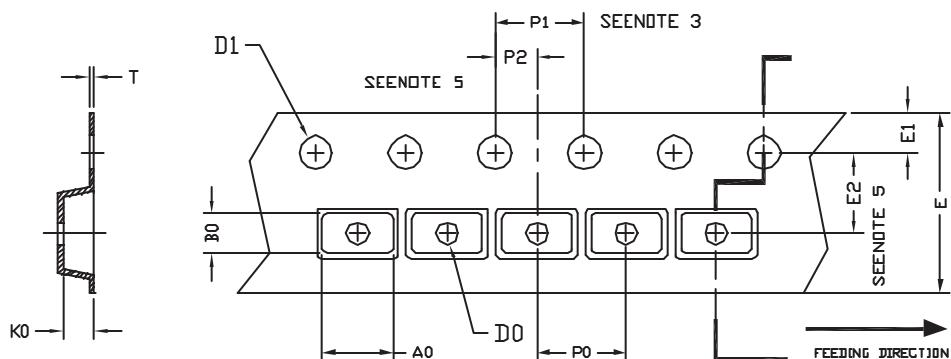


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.05	1.20	0.041	0.047
A1	0.05	0.15	0.002	0.006
A2	-	1.05	-	0.041
b	0.20	0.28	0.008	0.011
c	0.127		0.005	
D-8	2.90	3.10	0.114	0.122
E	4.30	4.50	0.169	0.177
E1	6.20	6.60	0.244	0.260
e	0.65BSC		0.025BSC	
L	0.50	0.70	0.020	0.028
L1	1.00		0.039	
θ ₁	0°	8°	0°	8°

STG8207

TSSOP-8 Tape and Reel Data

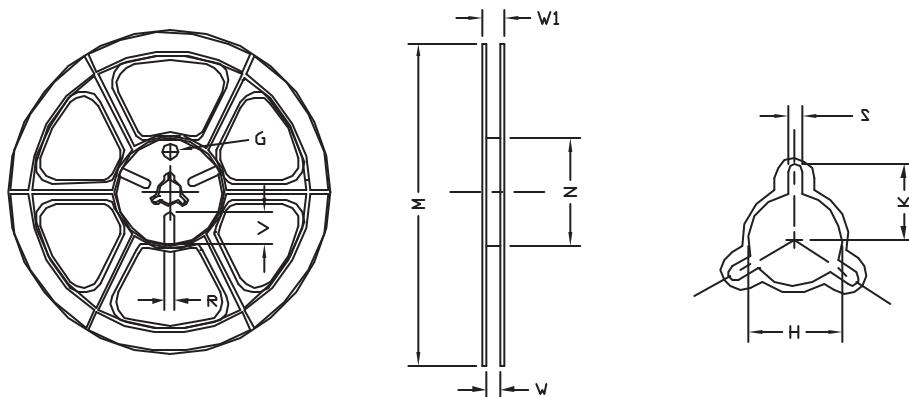
TSSOP-8 Carrier Tape



UNIT : mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TSSOP 8	6.08	4.40	1.60	$\phi 1.50$ + 0.1 - 0.0	$\phi 1.50$ + 0.1 - 0.0	12.00	1.75	5.50 ± 0.05	8.00	4.00	2.00 ± 0.05	0.30 ± 0.05

TSSOP-8 Reel



UNIT : mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330	100	12.5	16.0	$\phi 13.0$ + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---